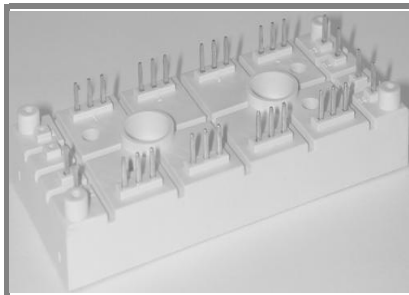


SKDH 116/..-L75



SEMIPONT™ 6

3-Phase Bridge Rectifier + IGBT braking chopper

SKDH 116/..-L75

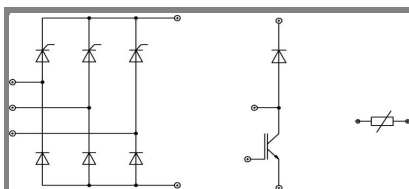
Preliminary Data

Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

Typical Applications*

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger



DH

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 110$ A (maximum value for continuous operation) ($T_s = 80$ °C)
1300	1200	SKDH 116/12-L75
1700	1600	SKDH 116/16-L75

Absolute Maximum Ratings		$T_s = 25$ °C, unless otherwise specified	
Symbol	Conditions	Values	Units
Bridge - Rectifier			
I_D	$T_s = 85$ °C; inductive load	110	A
I_{FSM}/I_{TSM}	$t_p = 10$ ms; sin 180 ; T_{jmax}	950	A
i^2t	$t_p = 10$ ms; sin 180 ; T_{jmax}	4500	A ² s
IGBT - Chopper			
V_{CES}/V_{GES}		1200 / 20	V
I_C	$T_s = 25$ (70) °C	100 (75)	A
I_{CM}	$t_p = 1$ ms; $T_s = 25$ (70) °C	200 (150)	A
Freewheeling - CAL Diode			
V_{RRM}		1200	V
I_F	$T_s = 25$ (70) °C	90 (70)	A
I_{FM}	$t_p = 1$ ms; $T_s = 25$ (70) °C	180 (140)	A
T_{vj}	Diode & IGBT (Thyristor)	- 40 ... + 150 (-40...+ 125)	°C
T_{stg}		- 40 ... + 125	°C
T_{solder}	terminals, 10 s	260	°C
V_{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V

Characteristics		$T_s = 25$ °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
Diode - Rectifier					
V_{TO} / r_t	$T_j = 125$ °C		0,8 / 7		V / mΩ
$R_{th(j-s)}$	per diode			1	K/W
Thyristor - Rectifier					
$V_{F(TO)} / r_t$	$T_j = 125$ °C		1,1 / 6		V / mΩ
$R_{th(j-s)}$	per Thyristor			0,84	K/W
I_{GD}	$T_j = 125$ °C; d.c.		5		mA
V_{GT} / I_{GT}	$T_j = 25$ °C			3 / 150	V / mA
I_H / I_L	$T_j = 25$ °C		250 / 600		mA
$(dv/dt)_{cr}$	$T_j = 125$ °C	500			V/μs
$(di/dt)_{cr}$	$T_j = 125$ °C			125	A/μs
IGBT - Chopper					
$V_{CE(sat)}$	$I_C = 75$ A, $T_j = 25$ °C; $V_{GE} = 15$ V		2,35		V
$R_{th(j-s)}$	per IGBT			0,4	K/W
$t_{d(on)} / t_r$	valid for all values:		113,8 / 94,4		ns
$t_{d(off)} / t_f$	$V_{CC} = 600$ V; $V_{GE} = 15$ V; $I_C = 90$ A; $T_j = 125$ °C;		845,4 / 94,4		ns
$E_{on} + E_{off}$	$T_j = 125$ °C; $R_G = 16$ Ω; inductive load		18,3		mJ
CAL - Diode - Freewheeling					
$V_{T(TO)} / r_t$	$T_j = 125$ °C		1 / 8	1,2 / 11	V / mΩ
$R_{th(j-s)}$	per diode			0,6	K/W
I_{RRM}	valid for all values:		65		A
Q_{rr}	$I_F = 100$ A; $V_R = - -600$ V; $di_F/dt = - -1000$ A/μs		15		μC
E_{off}	$V_{GE} = 0$ V; $T_j = 125$ °C				mJ
Temperature Sensor					
R_{TS}	$T = 25$ (100) °C;		1000 (1670)		Ω
Mechanical data					
M_S	mounting Torque		2,55	3,45	Nm

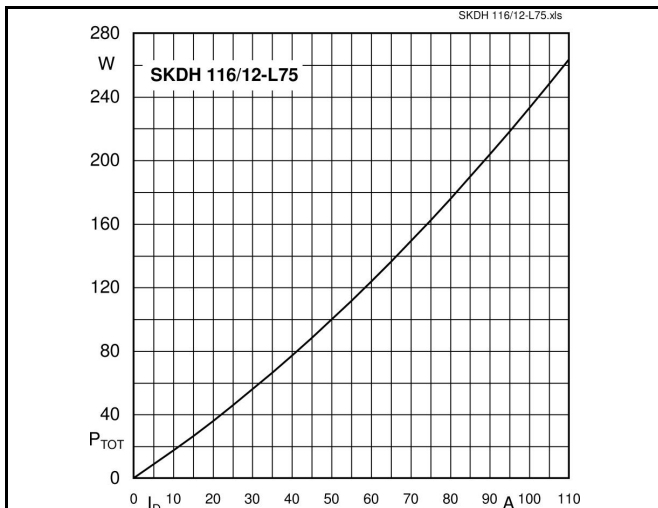


Fig. 1 Power dissipation per module vs. output current

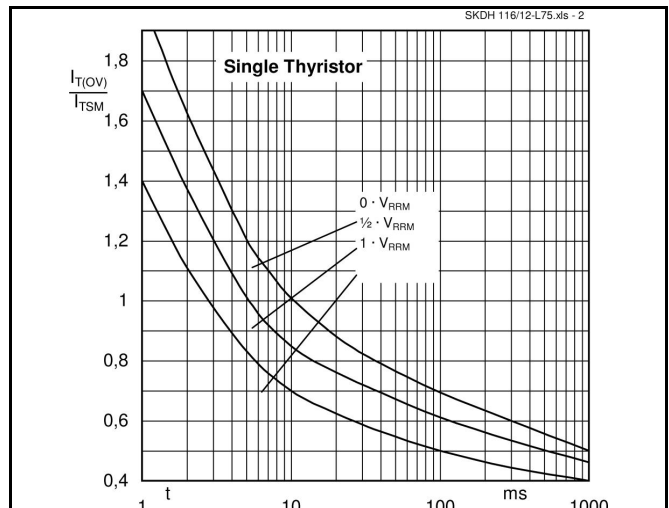


Fig. 2 Surge overload current vs. time

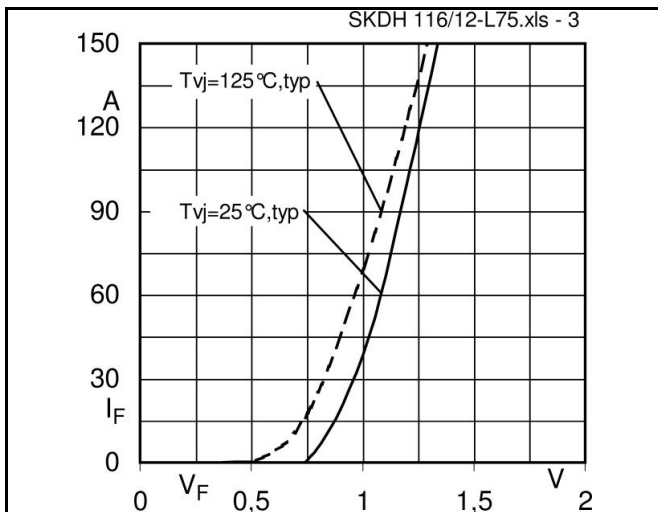


Fig. 3 Forward characteristic of single rectifier diode

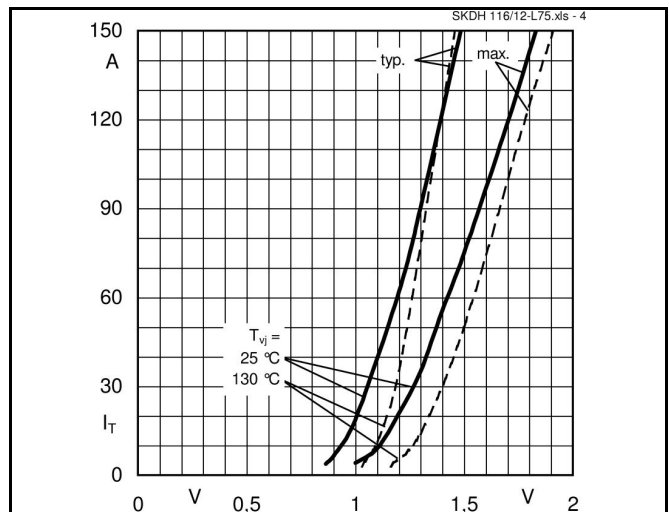


Fig. 4 Forward characteristic of single thyristor

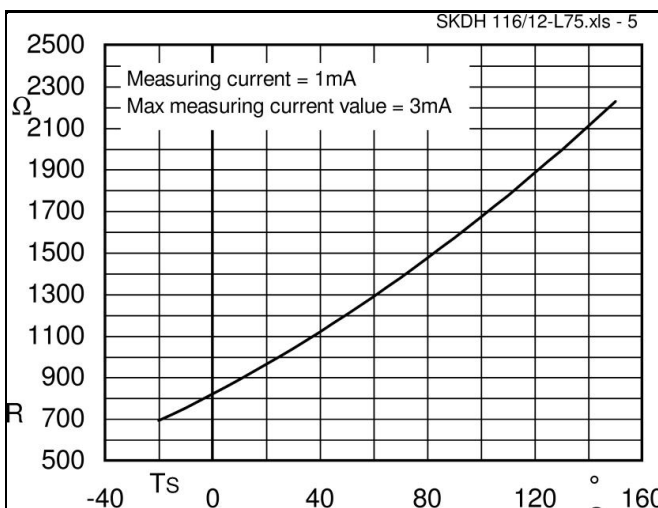


Fig. 5 Temperature sensor characteristic

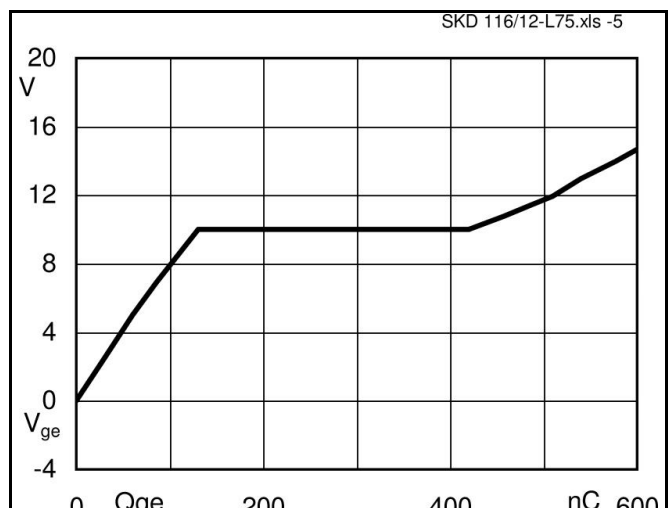
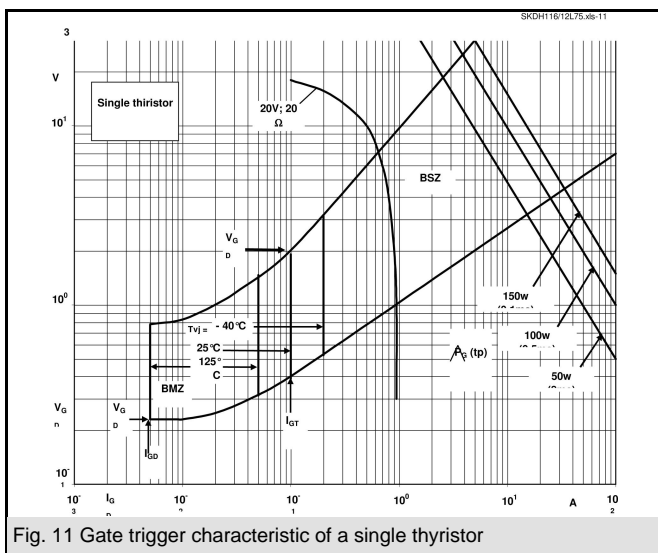
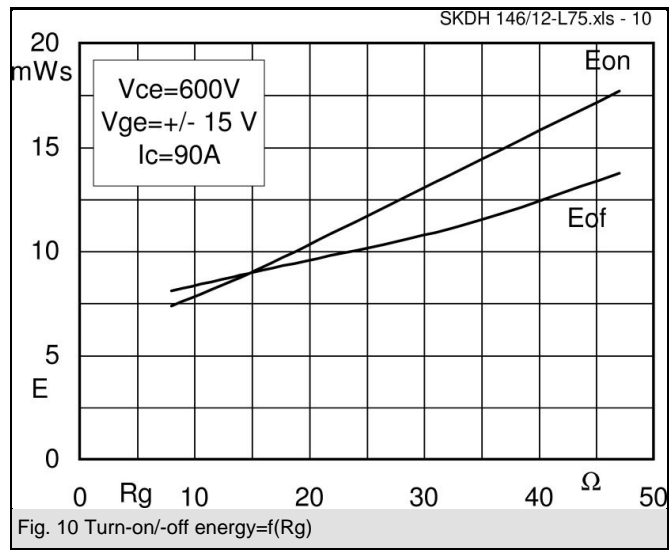
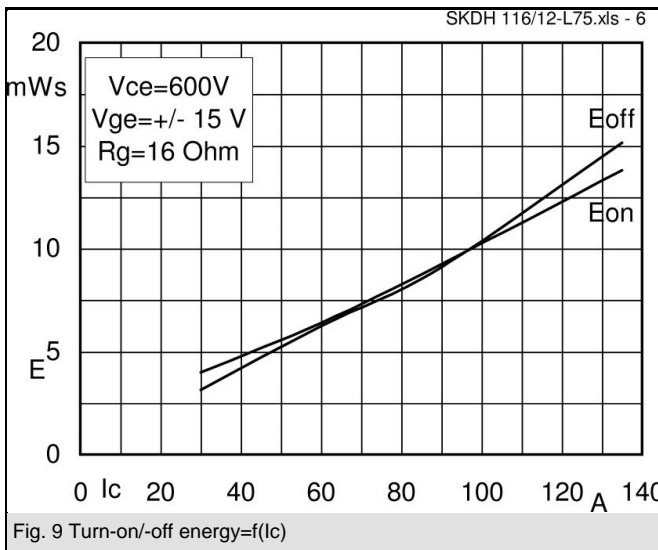
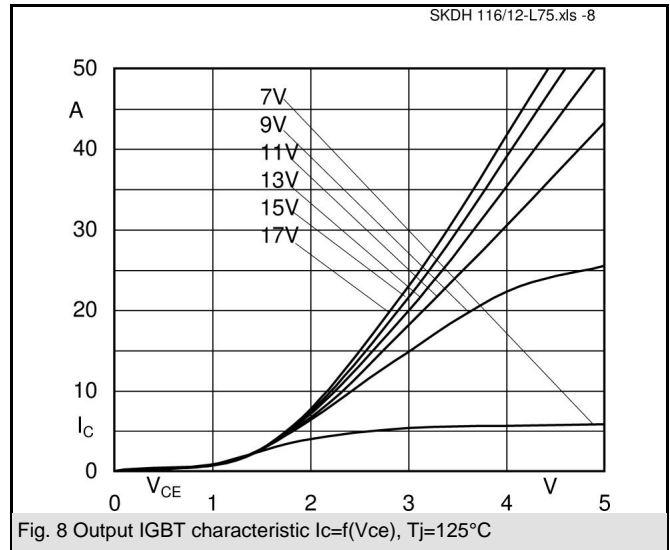
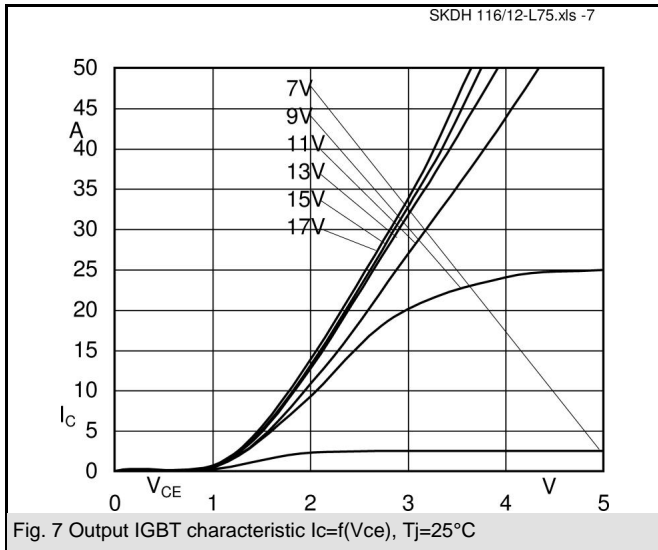


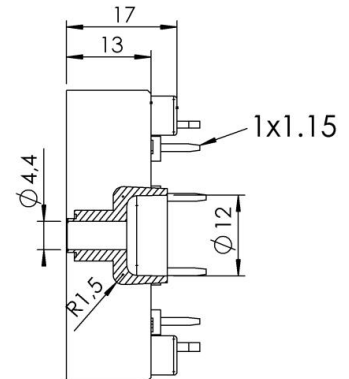
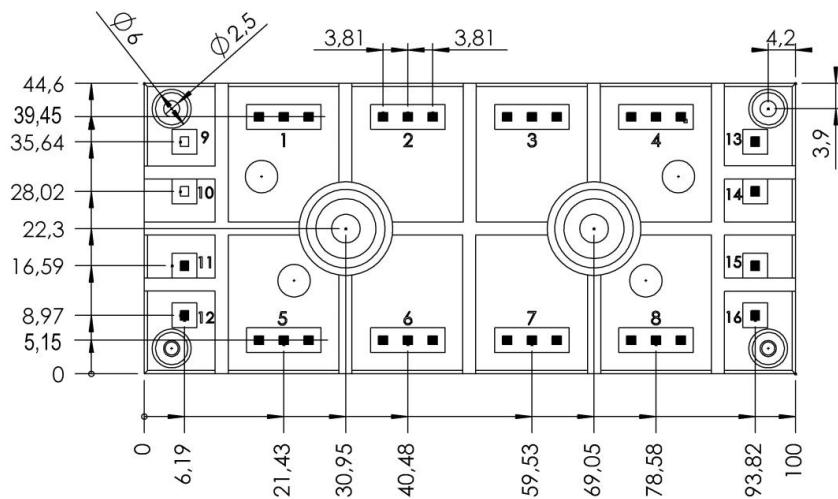
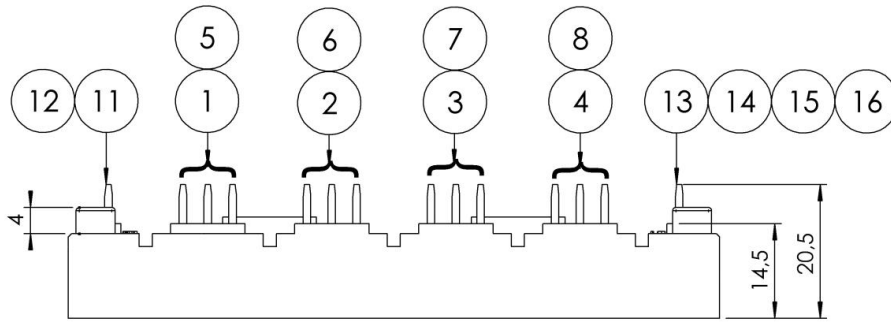
Fig. 6 Typ. gate charge characteristic



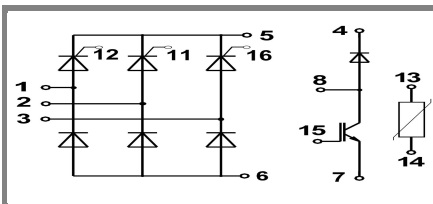
SKDH 116/..-L75

UL recognized
File n° E63 532

Dimensions in mm



Case G 59



Case G 59

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.